Digital Transistors (BRT) R1 = 100 kΩ, R2 = 100 kΩ

NPN Transistors with Monolithic Bias Resistor Network

MUN2236, MMUN2236L, MUN5236, DTC115EE, DTC115EM3

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base–emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

Features

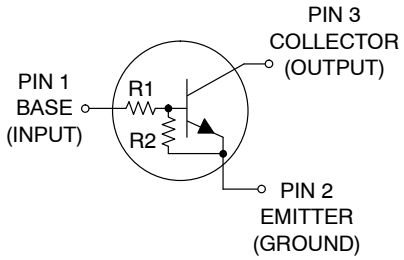
- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_A = 25°C)

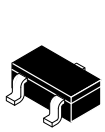
Rating	Symbol	Max	Unit
Collector–Base Voltage	V_{CBO}	50	Vdc
Collector–Emitter Voltage	V_{CEO}	50	Vdc
Collector Current – Continuous	I_C	100	mAdc
Input Forward Voltage	$V_{IN(fwd)}$	40	Vdc
Input Reverse Voltage	$V_{IN(rev)}$	10	Vdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

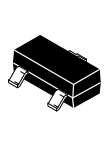
PIN CONNECTIONS



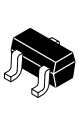
MARKING DIAGRAMS



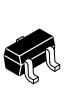
SC–59
CASE 318D
STYLE 1



SOT–23
CASE 318
STYLE 6



SC–70/SOT–323
CASE 419
STYLE 3



SC–75
CASE 463
STYLE 1



SOT–723
CASE 631AA
STYLE 1

XXX = Specific Device Code
M = Date Code*
▪ = Pb–Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending up-on manufacturing location.

ORDERING INFORMATION

See detailed ordering, marking, and shipping information in the package dimensions section on page 2 of this data sheet.

NOTE: Some of the devices on this data sheet have been **DISCONTINUED**. Please refer to the table on page 2.

© Semiconductor Components Industries, LLC, 2017

Table 1. ORDERING INFORMATION

Device	Part Marking	Package	Shipping†
NSVMUN2236T1G*	8N	SC−59 (Pb−Free)	3000 / Tape & Reel
MMUN2236LT1G, NSVMMUN2236LT1G*	AA5	SOT−23 (Pb−Free)	3000 / Tape & Reel
MUN5236T1G, NSVMUN5236T1G*	8N	SC−70/SOT−323 (Pb−Free)	3000 / Tape & Reel
DTC115EET1G	8N	SC−75 (Pb−Free)	3000 / Tape & Reel
DTC115EM3T5G	8N	SOT−723 (Pb−Free)	8000 / Tape & Reel

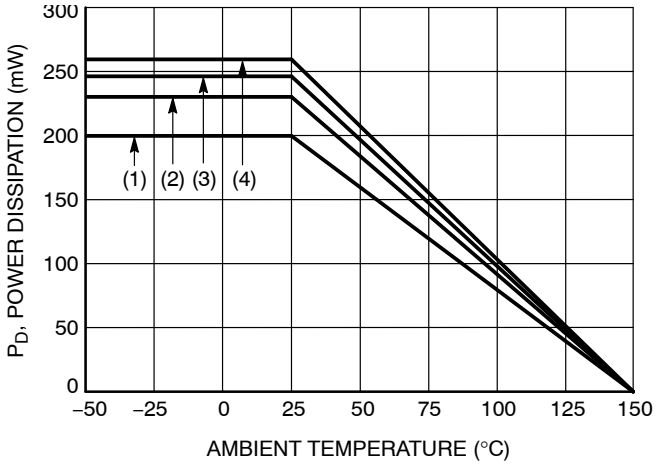
DISCONTINUED (Note 1)

MUN2236T1G	8N	SC−59 (Pb−Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

1. **DISCONTINUED:** This device is not recommended for new design. Please contact your **onsemi** representative for information. The most current information on this device may be available on www.onsemi.com.



(1) SC−75 and SC−70/SOT323; Minimum Pad
(2) SC−59; Minimum Pad
(3) SOT−23; Minimum Pad
(4) SOT−723; Minimum Pad

Figure 1. Derating Curve

Share Feedback
Your Opinion Matters

Table 2. THERMAL CHARACTERISTICS

Characteristic		Symbol	Max	Unit
THERMAL CHARACTERISTICS (SC−59) (MUN2236)				
Total Device Dissipation T_A = 25°C Derate above 25°C	 (Note 2) (Note 3) (Note 2) (Note 3)	P_D	 230 338 1.8 2.7	 mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 2) (Note 3)	$R_{\theta JA}$	540 370	°C/W
Thermal Resistance, Junction to Lead	(Note 2) (Note 3)	$R_{\theta JL}$	264 287	°C/W
Junction and Storage Temperature Range		T_J, T_{stg}	−55 to +150	°C
THERMAL CHARACTERISTICS (SOT−23) (MMUN2236L)				
Total Device Dissipation T_A = 25°C Derate above 25°C	 (Note 2) (Note 3) (Note 2) (Note 3)	P_D	 246 400 2.0 3.2	 mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 3)	$R_{\theta JA}$	508 311	°C/W
Thermal Resistance, Junction to Lead	(Note 2) (Note 3)	$R_{\theta JL}$	174 208	°C/W
Junction and Storage Temperature Range		T_J, T_{stg}	−55 to +150	°C
THERMAL CHARACTERISTICS (SC−70/SOT−323) (MUN5236)				
Total Device Dissipation T_A = 25°C Derate above 25°C	 (Note 2) (Note 3) (Note 2) (Note 3)	P_D	 202 310 1.6 2.5	 mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 2) (Note 3)	$R_{\theta JA}$	618 403	°C/W
Thermal Resistance, Junction to Lead	(Note 2) (Note 3)	$R_{\theta JL}$	280 332	°C/W
Junction and Storage Temperature Range		T_J, T_{stg}	−55 to +150	°C
THERMAL CHARACTERISTICS (SC−75) (DTC115EE)				
Total Device Dissipation T_A = 25°C Derate above 25°C	 (Note 2) (Note 3) (Note 2) (Note 3)	P_D	 200 300 1.6 2.4	 mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 2) (Note 3)	$R_{\theta JA}$	600 400	°C/W
Junction and Storage Temperature Range		T_J, T_{stg}	−55 to +150	°C
THERMAL CHARACTERISTICS (SOT−723) (DTC115EM3)				
Total Device Dissipation T_A = 25°C Derate above 25°C	 (Note 2) (Note 3) (Note 2) (Note 3)	P_D	 260 600 2.0 4.8	 mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 2) (Note 3)	$R_{\theta JA}$	480 205	°C/W
Junction and Storage Temperature Range		T_J, T_{stg}	−55 to +150	°C

2. FR−4 @ Minimum Pad.
3. FR−4 @ 1.0 x 1.0 Inch Pad.

Share Feedback
Your Opinion Matters

Table 3. ELECTRICAL CHARACTERISTICS (T_A = 25°C, unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector−Base Cutoff Current (V_{CB} = 50 V, I_E = 0)	I_{CBO}	–	–	100	nAdc
Collector−Emitter Cutoff Current (V_{CE} = 50 V, I_B = 0)	I_{CEO}	–	–	500	nAdc
Emitter−Base Cutoff Current (V_{EB} = 6.0 V, I_C = 0)	I_{EBO}	–	–	0.05	mAdc
Collector−Base Breakdown Voltage (I_C = 10 μA, I_E = 0)	$V_{(BR)CBO}$	50	–	–	Vdc
Collector−Emitter Breakdown Voltage (Note 4) (I_C = 2.0 mA, I_B = 0)	$V_{(BR)CEO}$	50	–	–	Vdc
ON CHARACTERISTICS					
DC Current Gain (Note 4) (I_C = 5.0 mA, V_{CE} = 10 V)	h_{FE}	80	150	–	
Collector−Emitter Saturation Voltage (Note 4) (I_C = 10 mA, I_B = 0.3 mA)	$V_{CE(sat)}$	–	–	0.25	Vdc
Input Voltage (off) (V_{CE} = 5.0 V, I_C = 100 μA)	$V_{i(off)}$	–	1.2	0.5	Vdc
Input Voltage (on) (V_{CE} = 0.3 V, I_C = 1.0 mA)	$V_{i(on)}$	3.0	1.7	–	Vdc
Output Voltage (on) (V_{CC} = 5.0 V, V_B = 5.5 V, R_L = 1.0 kΩ)	V_{OL}	–	–	0.2	Vdc
Output Voltage (off) (V_{CC} = 5.0 V, V_B = 0.25 V, R_L = 1.0 kΩ)	V_{OH}	4.9	–	–	Vdc
Input Resistor	R1	70	100	130	kΩ
Resistor Ratio	R_1/R_2	0.8	1.0	1.2	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle ≤ 2%.

Share Feedback
Your Opinion Matters

TYPICAL CHARACTERISTICS
MUN2236, MMUN2236L, MUN5236, NSVMUN5236, DTC115EE, DTC115EM3

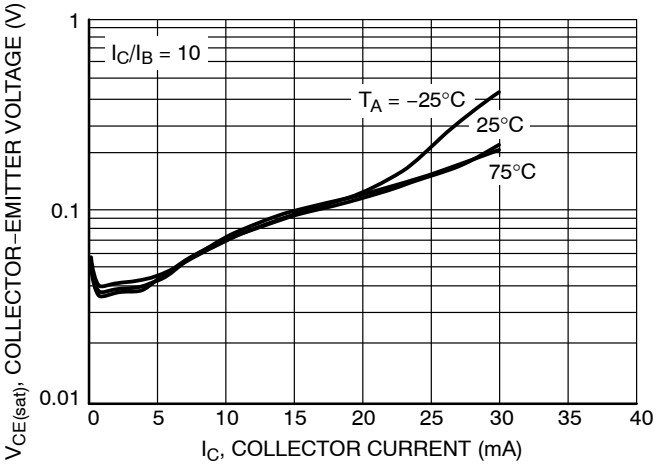


Figure 2. $V_{CE(sat)}$ versus I_C

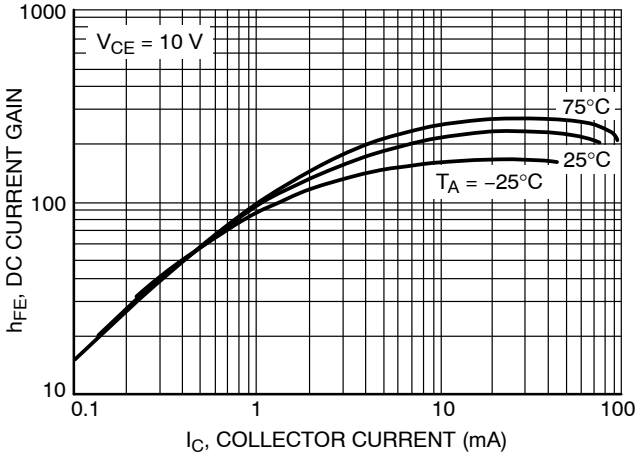


Figure 3. DC Current Gain

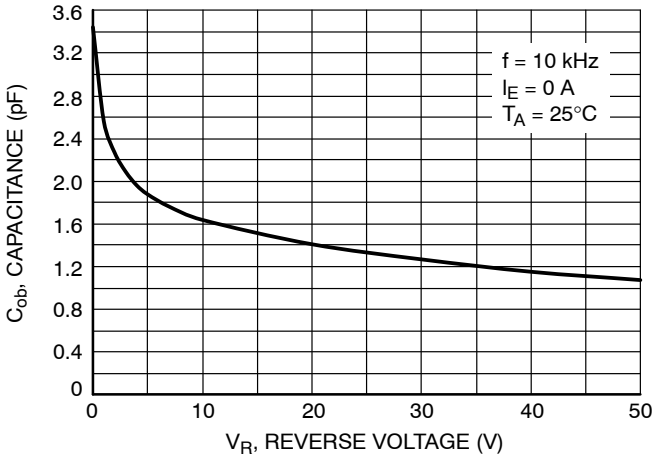


Figure 4. Output Capacitance

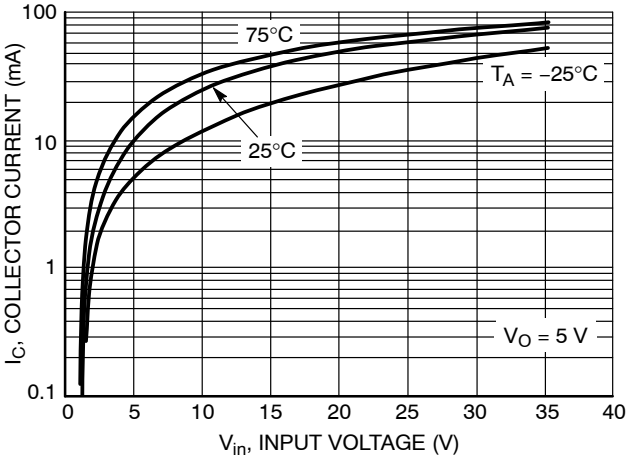


Figure 5. Output Current versus Input Voltage

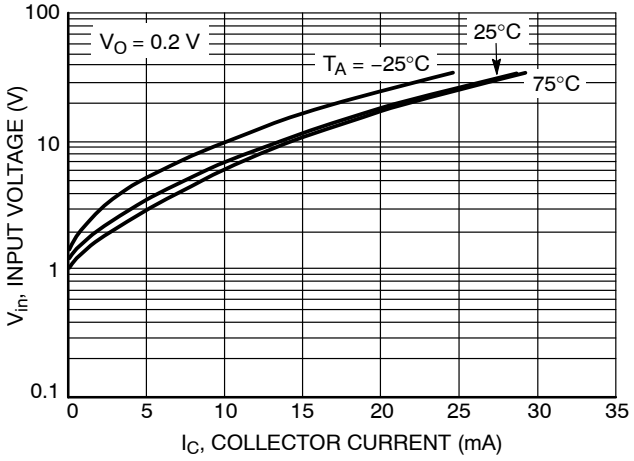
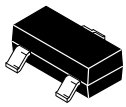


Figure 6. Input Voltage versus Output Current

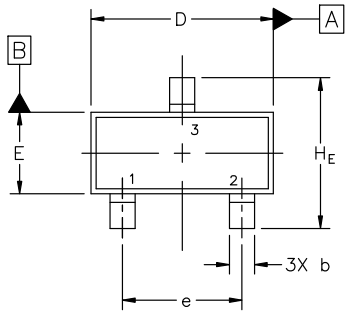
Share Feedback
Your Opinion Matters



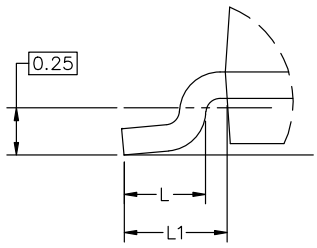
SCALE 4:1

SOT−23 (TO−236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

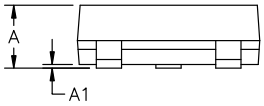
DATE 14 AUG 2024



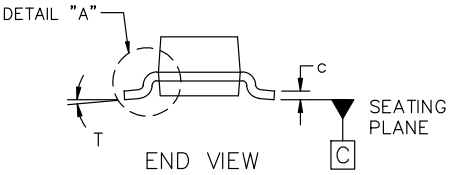
TOP VIEW



DETAIL "A"
Scale 3:1



SIDE VIEW

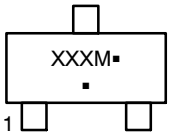


END VIEW

MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.89	1.00	1.11
A1	0.01	0.06	0.10
b	0.37	0.44	0.50
c	0.08	0.14	0.20
D	2.80	2.90	3.04
E	1.20	1.30	1.40
e	1.78	1.90	2.04
L	0.30	0.43	0.55
L1	0.35	0.54	0.69
H_E	2.10	2.40	2.64
T	0°	−−−	10°

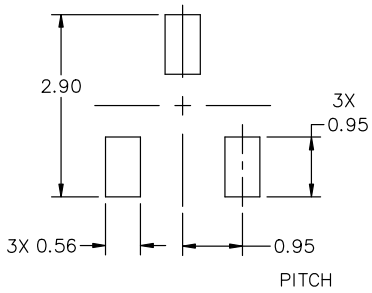
NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSIONS: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC
MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED
MOUNTING FOOTPRINT

* For additional information on our Pb−Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

DOCUMENT NUMBER:	**98ASB42226B**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	**SOT−23 (TO−236) 2.90x1.30x1.00 1.90P**		**PAGE 1 OF 2**

onsemi and onsemi are trademarks of Semiconductor Components Industries, LLC dba **onsemi** or its subsidiaries in the United States and/or other countries. **onsemi** reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

© Semiconductor Components Industries, LLC, 2019

SOT−23 (TO−236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5:
CANCELLED

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE−ANODE

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE

STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE

STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE−ANODE

STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT

STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE

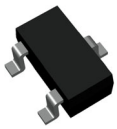
STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION

STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE

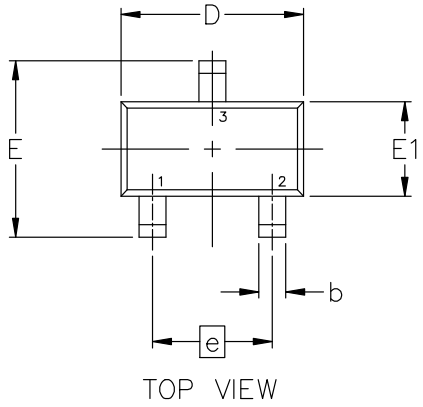
onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba **onsemi** or its subsidiaries in the United States and/or other countries. **onsemi** reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

© Semiconductor Components Industries, LLC, 2019

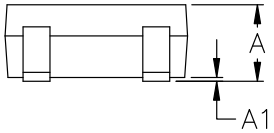


SC−59−3 2.90x1.50x1.15, 1.90P
CASE 318D
ISSUE J

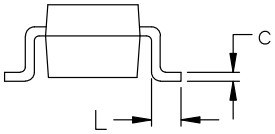
DATE 15 FEB 2024



TOP VIEW



SIDE VIEW

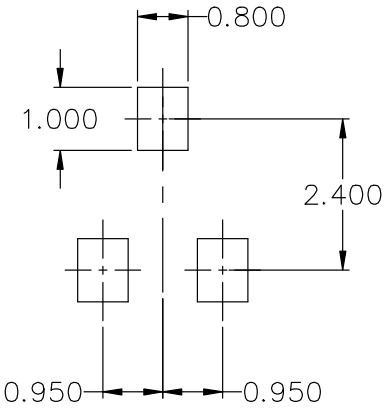


END VIEW

NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5−2018.
2. ALL DIMENSION ARE IN MILLIMETERS.

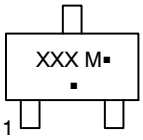
DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	1.00	1.15	1.30
A1	0.01	0.06	0.10
b	0.35	0.43	0.50
c	0.09	0.14	0.18
D	2.70	2.90	3.10
E	2.50	2.80	3.00
E1	1.30	1.50	1.70
e	1.90 BSC		
L	0.20	0.40	0.60



RECOMMENDED MOUNTING FOOTPRINT*

* FOR ADDITIONAL INFORMATION ON OUR Pb−FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package*

(*Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 2:
PIN 1. ANODE
2. N.C.
3. CATHODE

STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 4:
PIN 1. CATHODE
2. N.C.
3. ANODE

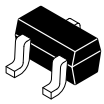
STYLE 5:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 6:
PIN 1. ANODE
2. CATHODE
3. ANODE/CATHODE

DOCUMENT NUMBER:	**98ASB42664B**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.
DESCRIPTION:	**SC−59−3 2.90x1.50x1.15, 1.90P**	**PAGE 1 OF 1**

onsemi and onsemi are trademarks of Semiconductor Components Industries, LLC dba **onsemi** or its subsidiaries in the United States and/or other countries. **onsemi** reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

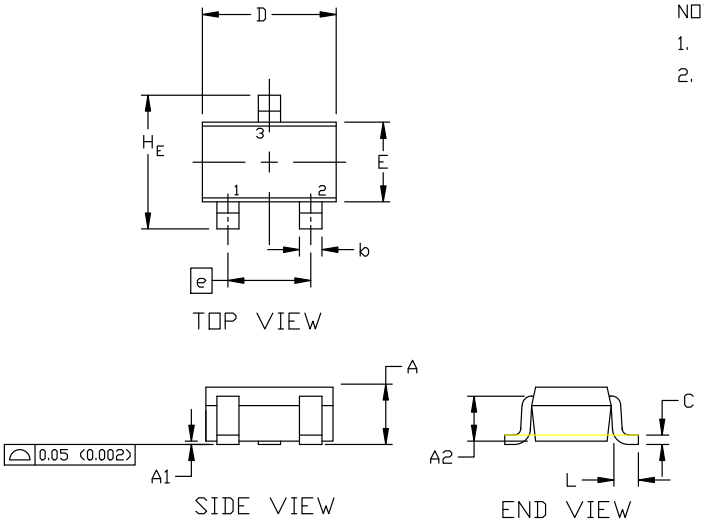
© Semiconductor Components Industries, LLC, 2000



SCALE 4:1

SC−70 (SOT−323)
CASE 419
ISSUE R

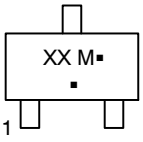
DATE 11 OCT 2022



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH

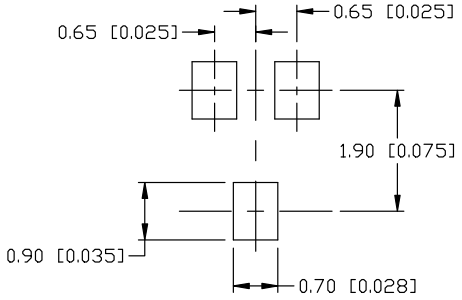
	MILLIMETERS			INCHES		
DIM	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
H_E	2.00	2.10	2.40	0.079	0.083	0.095

GENERIC MARKING DIAGRAM



XX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.



* For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

SOLDERING FOOTPRINT

STYLE 1:
CANCELLED

STYLE 2:
PIN 1. ANODE
2. N.C.
3. CATHODE

STYLE 3:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 5:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 6:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 7:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 8:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 9:
PIN 1. ANODE
2. CATHODE
3. CATHODE−ANODE

STYLE 10:
PIN 1. CATHODE
2. ANODE
3. ANODE−CATHODE

STYLE 11:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

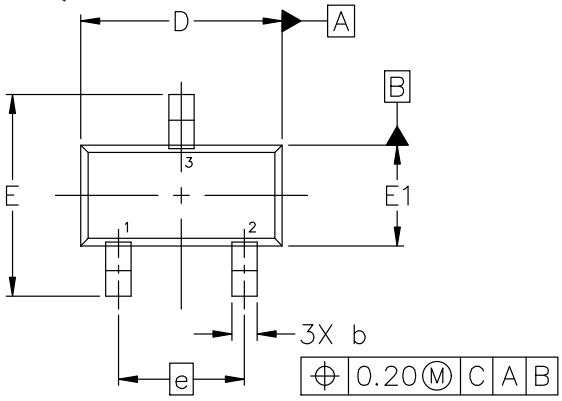
DOCUMENT NUMBER:	**98ASB42819B**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.
DESCRIPTION:	**SC−70 (SOT−323)**	**PAGE 1 OF 1**

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba **onsemi** or its subsidiaries in the United States and/or other countries. **onsemi** reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

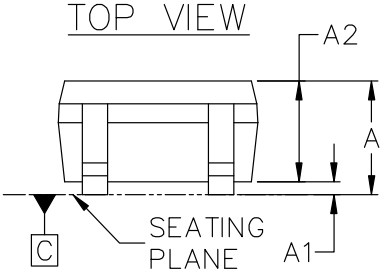
SC75−3 1.60x0.80x0.80, 1.00P
CASE 463
ISSUE H

DATE 01 FEB 2024

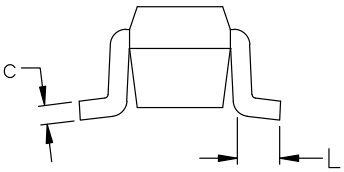




TOP VIEW



SIDE VIEW



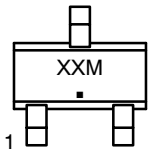
END VIEW

NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5−2018.
2. ALL DIMENSION ARE IN MILLIMETERS.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.70	0.80	0.90
A1	0.00	0.05	0.10
A2		0.80 REF.	
b	0.15	0.20	0.30
c	0.10	0.15	0.25
D	1.55	1.60	1.65
E	1.50	1.60	1.70
E1	0.70	0.80	0.90
e		1.00 BSC	
L	0.10	0.15	0.20

GENERIC
MARKING DIAGRAM*



XX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

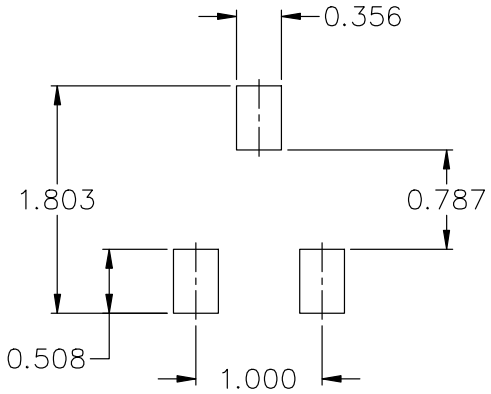
STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 2:
PIN 1. ANODE
2. N/C
3. CATHODE

STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 5:
PIN 1. GATE
2. SOURCE
3. DRAIN



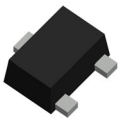
RECOMMENDED MOUNTING FOOTPRINT*

* FOR ADDITIONAL INFORMATION ON OUR Pb−FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

DOCUMENT NUMBER:	98ASB15184C	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.
DESCRIPTION:	SC75−3 1.60x0.80x0.80, 1.00P	PAGE 1 OF 1

onsemi and onsemi are trademarks of Semiconductor Components Industries, LLC dba **onsemi** or its subsidiaries in the United States and/or other countries. **onsemi** reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

© Semiconductor Components Industries, LLC, 1996

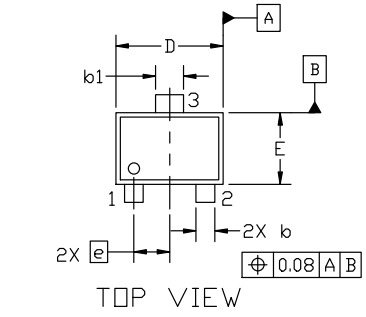


SOT−723 1.20x0.80x0.50, 0.40P
CASE 631AA
ISSUE E

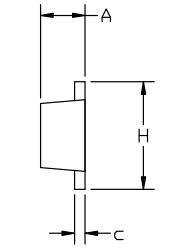
DATE 24 JAN 2024

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

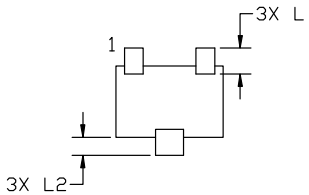
DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.45	0.50	0.55
b	0.15	0.21	0.27
b1	0.25	0.31	0.37
c	0.07	0.12	0.17
D	1.15	1.20	1.25
E	0.75	0.80	0.85
e	0.40 BSC		
H	1.15	1.20	1.25
L	0.29 REF		
L2	0.15	0.20	0.25



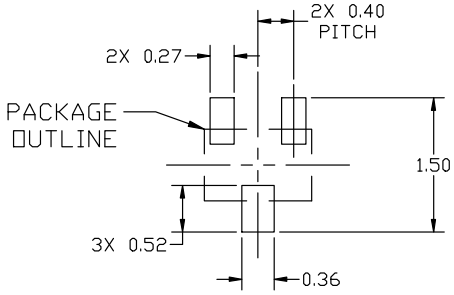
TOP VIEW



SIDE VIEW



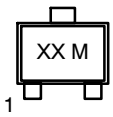
BOTTOM VIEW



RECOMMENDED MOUNTING
FOOTPRINT

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC
MARKING DIAGRAM*



XX = Specific Device Code
M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 2:
PIN 1. ANODE
2. N/C
3. CATHODE

STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 5:
PIN 1. GATE
2. SOURCE
3. DRAIN

DOCUMENT NUMBER:	**98AON12989D**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.
DESCRIPTION:	**SOT−723 1.20x0.80x0.50, 0.40P**	**PAGE 1 OF 1**

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba **onsemi** or its subsidiaries in the United States and/or other countries. **onsemi** reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

onsemi, , and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent−Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as−is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical−documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales